# Old Company Name in Catalogs and Other Documents

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April 1<sup>st</sup>, 2010 Renesas Electronics Corporation

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# H5N3007CF

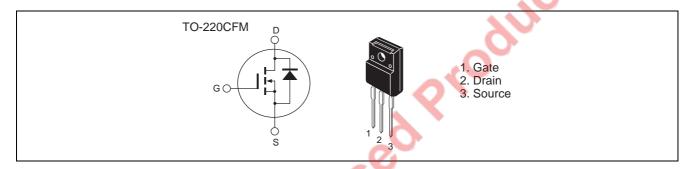
# Silicon N Channel MOS FET High Speed Power Switching

REJ03G0473-0100 Rev.1.00 Nov.11.2004

### **Features**

- Low on-resistance
- Low leakage current
- High Speed Switching
- Built-in fast recovery diode

### **Outline**



# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

| Item                                        | Symbol                        | Ratings     | Unit |
|---------------------------------------------|-------------------------------|-------------|------|
| Drain to source voltage                     | V <sub>DSS</sub>              | 300         | V    |
| Gate to source voltage                      | $V_{GSS}$                     | ±30         | V    |
| Drain current                               | $I_D$                         | 15          | A    |
| Drain peak current                          | I <sub>D(pulse)</sub> Note 1  | 60          | A    |
| Body-drain diode reverse drain current      | I <sub>DR</sub>               | 15          | A    |
| Body-drain diode reverse drain peak current | I <sub>DR(pulse)</sub> Note 1 | 60          | A    |
| Avalanche current                           | I <sub>AP</sub> Note 3        | 15          | A    |
| Channel dissipation                         | Pch Note 2                    | 35          | W    |
| Channel to case Thermal Impedance           | θch-c                         | 3.57        | °C/W |
| Channel temperature                         | Tch                           | 150         | °C   |
| Storage temperature                         | Tstg                          | -55 to +150 | °C   |

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tc = 25°C
- 3. Tch ≤ 150°C

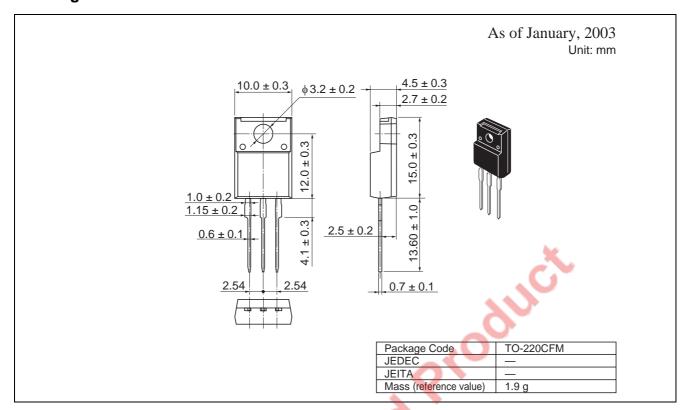
## **Electrical Characteristics**

 $(Ta = 25^{\circ}C)$ 

| Item                                       | Symbol              | Min | Тур  | Max  | Unit | Test Conditions                                              |
|--------------------------------------------|---------------------|-----|------|------|------|--------------------------------------------------------------|
| Drain to source breakdown voltage          | $V_{(BR)DSS}$       | 300 | _    | _    | V    | $I_D = 10 \text{ mA}, V_{GS} = 0$                            |
| Gate to source leak current                | I <sub>GSS</sub>    | _   |      | ±0.1 | μΑ   | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$                      |
| Zero gate voltage drain current            | I <sub>DSS</sub>    | _   | _    | 10   | μΑ   | $V_{DS} = 300 \text{ V}, V_{GS} = 0$                         |
| Gate to source cutoff voltage              | $V_{GS(off)}$       | 1.5 | _    | 4.0  | V    | $I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$                  |
| Static drain to source on state resistance | R <sub>DS(on)</sub> | _   | 0.12 | 0.16 | Ω    | $I_D = 7.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note 4}}$ |
| Forward transfer admittance                | y <sub>fs</sub>     | 9   | 15   | _    | S    | $I_D = 7.5 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note 4}}$ |
| Input capacitance                          | Ciss                | _   | 2180 | _    | pF   | V <sub>DS</sub> = 25 V                                       |
| Output capacitance                         | Coss                | _   | 275  | _    | pF   | $V_{GS} = 0$                                                 |
| Reverse transfer capacitance               | Crss                | _   | 77   | _    | pF   | f = 1MHz                                                     |
| Turn-on delay time                         | t <sub>d(on)</sub>  | _   | 35   | _    | ns   | I <sub>D</sub> = 7.5 A                                       |
| Rise time                                  | t <sub>r</sub>      | _   | 50   | _    | ns   | $R_L = 20 \Omega$                                            |
| Turn-off delay time                        | t <sub>d(off)</sub> | _   | 160  | _    | ns   | $V_{GS} = 10 \text{ V}$                                      |
| Fall time                                  | t <sub>f</sub>      | _   | 40   | _    | ns   | $R_g = 10 \Omega$                                            |
| Total gate charge                          | Qg                  | _   | 81   | _    | nC   | V <sub>DD</sub> = 240 V                                      |
| Gate to source charge                      | Qgs                 | _   | 10   | _    | nC   | $V_{GS} = 10 \text{ V}$                                      |
| Gate to drain charge                       | Qgd                 | _   | 38   | _    | nC   | I <sub>D</sub> = 15 A                                        |
| Body-drain diode forward voltage           | $V_{DF}$            | _   | 0.85 | 1.3  | V    | $I_F = 15 \text{ A}, V_{GS} = 0^{\text{Note4}}$              |
| Body-drain diode reverse recovery time     | t <sub>rr</sub>     | _   | 110  |      | ns   | $I_F = 15 \text{ A}, V_{GS} = 0$<br>diF/ dt = 100 A/ $\mu$ s |
| Body-drain diode reverse recovery time     | Qrr                 | _   | 0.44 |      | μС   |                                                              |

Notes: 4. Pulse test

# **Package Dimensions**



# **Ordering Information**

| Part Name | Quantity | Shipping Container |
|-----------|----------|--------------------|
| H5N3007CF | 50       | Stick              |

Note: Therefore especially small contact area of terminal, miss contact may occur if inadequate soldering condition is applied.

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